

BF398 is PNP silicon transistor designed for high voltage applications.

TO-92F



CBE

ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	VCBO	150V
Collector-Emitter Voltage	VCEO	150V
Emitter-Base Voltage	VEBO	6V
Total Power Dissipation	P _{tot}	625mW
Collector Current	I _C	100mA
Operating Junction & Storage Temperature	T _j , T _{stg}	-55 to +150°C

ELECTRICAL CHARACTERISTICS (T_a=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Collector-Base Breakdown Voltage	BVCBO	150		V	I _C =10μA I _E =0
Collector-Emitter Breakdown Voltage	LVCEO	150		V	I _C =10mA I _B =0
Emitter-Base Breakdown Voltage	BVEBO	6		V	I _E =10μA I _C =0
Collector Cutoff Current	ICBO		50	nA	V _{CB} =100V I _E =0
Emitter Cutoff Current	IEBO		50	nA	V _{EB} =4V I _C =0
D.C. Current Gain	HFE	25			I _C =1mA V _{CE} =10V
		30	200		I _C =10mA V _{CE} =10V
		20			I _C =100mA V _{CE} =10V
Base-Emitter Saturation Voltage	V _{BE(sat)}	0.6	0.9	V	I _C =10mA I _B =1mA
Collector-Emitter Saturation Voltage	V _{CE(sat)}		0.5	V	I _C =10mA I _B =1mA



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